DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **ESD Protected Gate, 1KV (HBM)**
- **Lead Free/RoHS Compliant (Note 1)**
- **Qualified to AEC-Q101 Standards for High Reliability**

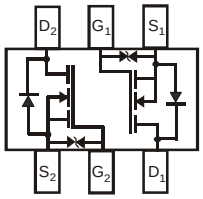
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

ESD PROTECTED TO 1kV

SOT363

Top View



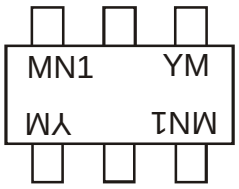
Top View
Internal Schematic

Ordering Information (Note 2)

Part Number	Case	Packaging
DMN66D0LDW-7	SOT363	3000/Tape & Reel

Notes: 1. No purposefully added lead.
2. For packaging details, go to our website at http://www.diodes.com.

Marking Information



MN1 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: U = 2007)
M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage (Note 3)	Continuous	V_{GSS}	±20	V
Drain Current (Note 3)	Continuous Continuous @ 100°C Pulsed	I_D	115 73 800	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation Derating above T_A = 25°C (Note 3)	P_D	250 1.6	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage		BV_{DSS}	60	70	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current	@ T_C = 25°C @ T_C = 125°C	I_{DSS}	—	—	1.0 500	μA	V_{DS} = 60V, V_{GS} = 0V
Gate-Body Leakage		I_{GSS}	—	—	±5	μA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage		$V_{GS(th)}$	1.2	—	2.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	@ T_J = 25°C	$R_{DS\ (ON)}$	—	3.5	6	Ω	V_{GS} = 5.0V, I_D = 0.115A
	@ T_J = 125°C			3.0	5		V_{GS} = 10V, I_D = 0.115A
Forward Transconductance		g_{FS}	80	V_{SD}	—	mS	V_{DS} = 10V, I_D = 0.115
Diode Forward Voltage		V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{iss}	—	23	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance		C_{oss}	—	3.4	—	pF	
Reverse Transfer Capacitance		C_{rss}	—	1.4	—	pF	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	—	10	—	ns	V_{DD} = 30V, I_D = 0.115A, R_L = 150Ω,
Turn-Off Delay Time		$t_{D(OFF)}$	—	33	—	ns	V_{GEN} = 10V, R_{GEN} = 25Ω

Notes: 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.
4. Short duration pulse test used to minimize self-heating effect.

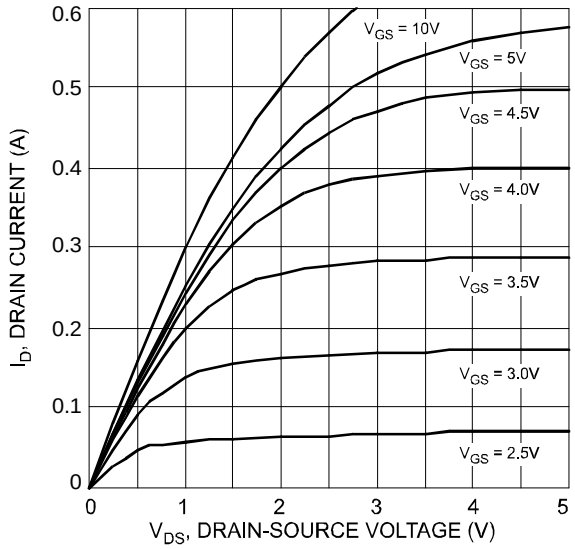


Fig.1 Typical Output Characteristic

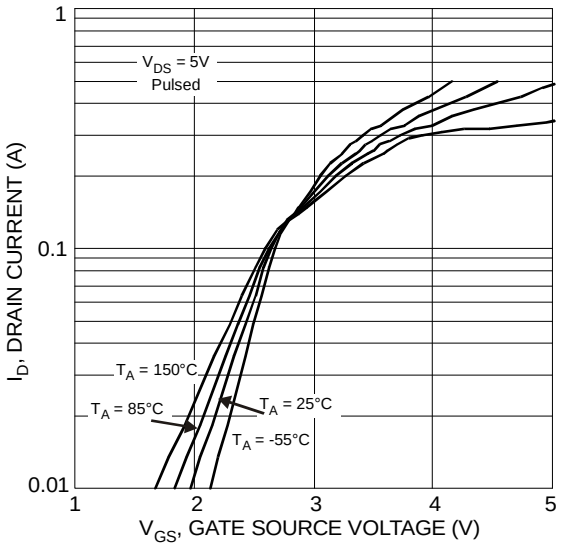


Fig. 2 Typical Transfer Characteristics

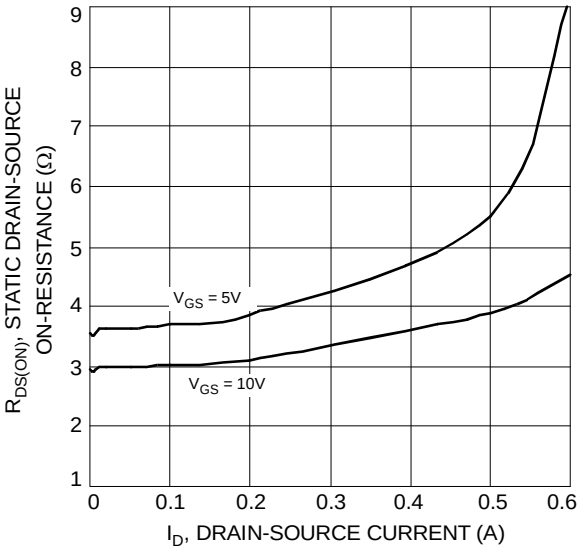


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

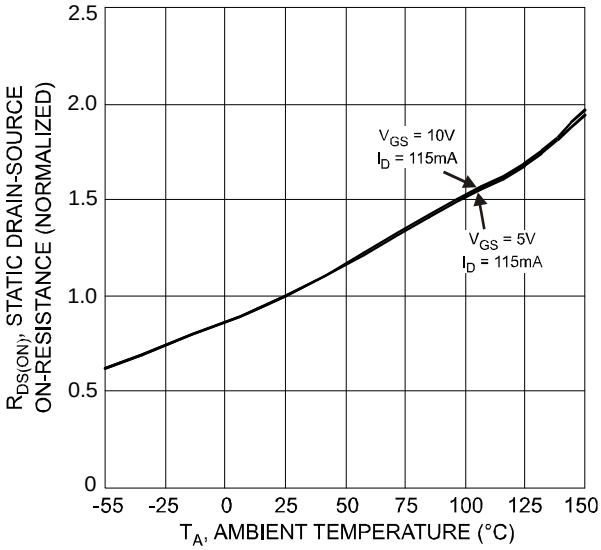


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

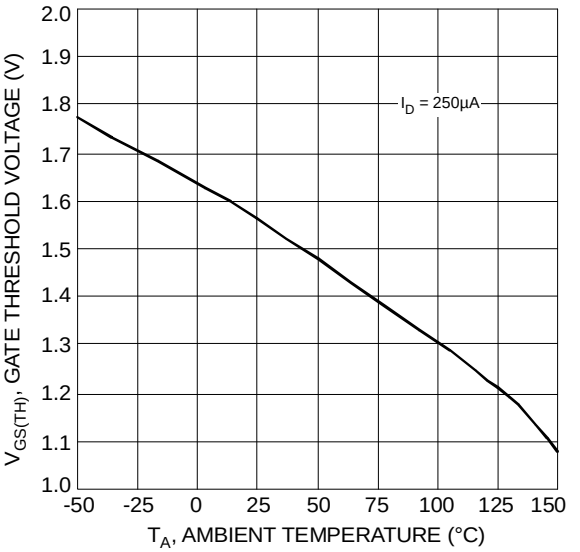


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

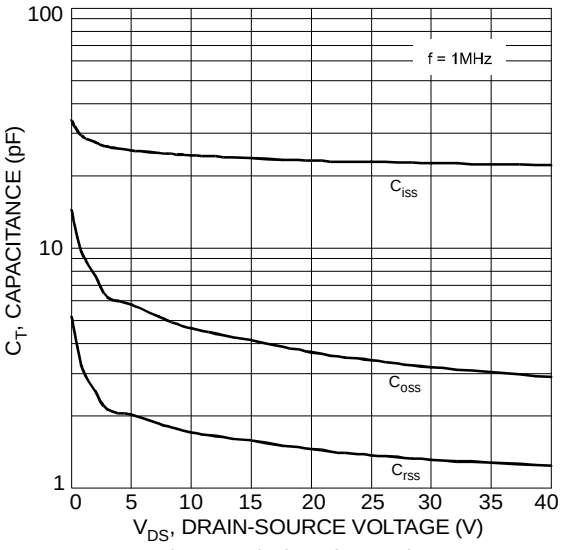


Fig. 6 Typical Total Capacitance

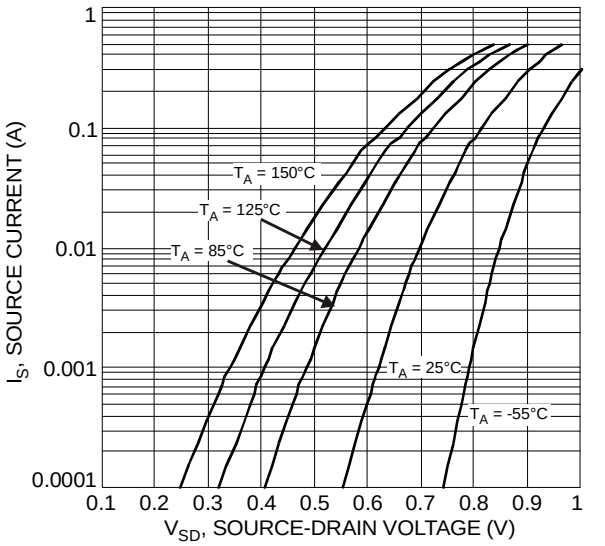
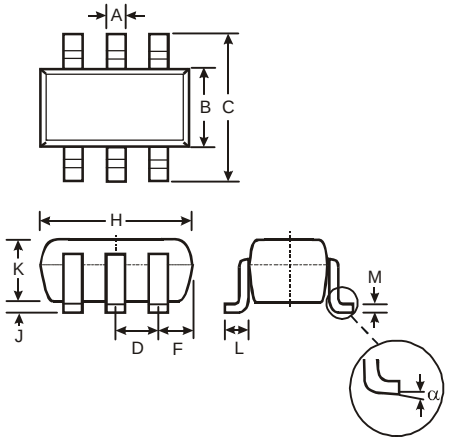


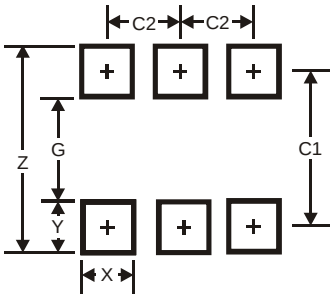
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Package Outline Dimensions



SOT363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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